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(57) **ABSTRACT**

A method of manufacturing a memory structure is provided. The method includes forming a first gate structure, a second gate structure, and a plurality of source/drain regions in a substrate, in which the plurality of source/drain regions are disposed on opposite sides of the first gate structure and the second gate structures; performing a dry etching process to form a trench between the first gate structure and the second gate structure; performing a wet etching process to expand the trench, in which the expanded trench has a hexagonal shaped cross section profile; and forming a bit line contact in the expanded trench.

